Yasuhiko Imai

List of Publications by Year in descending order

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933447 610901 32 568 10 24 citations h-index g-index papers 32 32 32 1068 all docs docs citations times ranked citing authors

#	Article	IF	CITATIONS
1	Position and electric field dependent local lattice strain detected by nanobeam x-ray diffraction on a relaxor ferroelectric single crystal. Physical Review B, 2022, 105, .	3.2	2
2	Analysis of inverse-piezoelectric-effect-induced lattice deformation in AlGaN/GaN high-electron-mobility transistors by time-resolved synchrotron radiation nanobeam X-ray diffraction. Applied Physics Express, 2021, 14, 095502.	2.4	2
3	Time-Resolved Nanobeam X-ray Diffraction of a Relaxor Ferroelectric Single Crystal under an Alternating Electric Field. Crystals, 2021, 11, 1419. Ferroelastic domain motion by pulsed electric field in <mml:math< td=""><td>2.2</td><td>3</td></mml:math<>	2.2	3
4	xmlns:mml="http://www.w3.org/1998/Math/MathML"> <mml:mrow><mml:mrow><mml:mo>(</mml:mo><mml: rhombohedral epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Pb</mml:mi><mml:mrow><.</mml:mrow></mml:mrow></mml:math </mml: </mml:mrow></mml:mrow>	mn>11	1 <mn 3</mn
5	Physical Review B, 2019, 100, . Current status of nanobeam x-ray diffraction station at SPring-8. AIP Conference Proceedings, 2019, , .	0.4	2
6	Quantitative analysis of lattice plane microstructure in the growth direction of a modified Na-flux GaN crystal using nanobeam X-ray diffraction. Japanese Journal of Applied Physics, 2019, 58, SCCB16.	1.5	4
7	xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"> <mml:mrow><mml:mi>Pb</mml:mi><mml:mo stretchy="false">(<mml:mi>Zr</mml:mi><mml:mo>,</mml:mo><mml:mi>Ti</mml:mi><mml:mo) i<="" td="" tj=""><td>ΞΤ<mark>ζ</mark>ά[§] :</td><td>1 0.78¹4314 rgBT</td></mml:mo)></mml:mo </mml:mrow>	ΞΤ <mark>ζ</mark> ά [§] :	1 0.78 ¹ 4314 rgBT
8	mathyariant="normal">Ox/mmkmi>x/mmkmrow>xmmkmrow>xmmkmrow>x/mmkmro	ub>0.4	ml:mrow>O
9	Depth-resolved analysis of lattice distortions in high-Ge-content SiGe/compositionally graded SiGe films using nanobeam x-ray diffraction. Semiconductor Science and Technology, 2018, 33, 124005.	2.0	3
10	Time response demonstration of in situ lattice deformation under an applied electric field by synchrotron-based time-resolved X-ray diffraction in polar-axis-oriented epitaxial Pb(Zr,Ti)O3 film. Japanese Journal of Applied Physics, 2018, 57, 0902B8.	1.5	2
11	Fabrication of tensile-strained single-crystalline GeSn on transparent substrate by nucleation-controlled liquid-phase crystallization. Applied Physics Letters, 2017, 110, .	3.3	16
12	Tomographic Mapping Analysis in the Depth Direction of High-Ge-Content SiGe Layers with Compositionally Graded Buffers Using Nanobeam X-ray Diffraction. ACS Applied Materials & Samp; Interfaces, 2017, 9, 13726-13732.	8.0	6
13	Effect of the film thickness on the crystal structure and ferroelectric properties of (Hf 0.5 Zr 0.5)O 2 thin films deposited on various substrates. Materials Science in Semiconductor Processing, 2017, 70, 239-245.	4.0	41
14	Electric-field-induced lattice distortion in epitaxial BiFeO3 thin films as determined by <i>in situ</i> time-resolved x-ray diffraction. Applied Physics Letters, 2017, 111, .	3.3	3
15	In-situ observation of ultrafast $90\hat{A}^\circ$ domain switching under application of an electric field in (100)/(001)-oriented tetragonal epitaxial Pb(Zr0.4Ti0.6)O3 thin films. Scientific Reports, 2017, 7, 9641.	3.3	23
16	Extended Polymorphism of Two-Dimensional Material. Nano Letters, 2017, 17, 5567-5571.	9.1	25
17	Domain Size of Phase-Separated NaxCoO2 as Investigated by X-Ray Microdiffraction. Batteries, 2017, 3, 5.	4.5	4
18	Quantification of local strain distributions in nanoscale strained SiGe FinFET structures. Journal of Applied Physics, 2017, 122, .	2.5	9

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19	Impact of mechanical stress on ferroelectricity in (Hf0.5Zr0.5)O2 thin films. Applied Physics Letters, 2016, 108, .	3.3	187
20	Characterization of domain structure in one-dimensional SrRuO3 nanostructure using synchrotron x-ray microdiffraction. AIP Conference Proceedings, 2016, , .	0.4	8
21	Large irreversible non- $180 {\hat A}^\circ$ domain switching after poling treatment in Pb(Zr, Ti)O3 films. Applied Physics Letters, 2016, 108, .	3.3	10
22	High-Pressure-Hydrogen-Induced Spin Reconfiguration in GdFe2 Observed by 57Fe-Polarized Synchrotron Radiation Mössbauer Spectroscopy with Nuclear Bragg Monochromator. Journal of the Physical Society of Japan, 2016, 85, 123707.	1.6	2
23	Positional dependence of defect distribution in semipolar hydride vapor phase epitaxy-GaN films grown on patterned sapphire substrates. Japanese Journal of Applied Physics, 2016, 55, 05FA07.	1.5	3
24	Microstructural analysis of an epitaxial AlN thick film/trench-patterned template by three-dimensional reciprocal lattice space mapping technique. Applied Physics Express, 2016, 9, 111001.	2.4	6
25	Parabolic refractive X-ray lenses made of quartz glass for high-energy X-ray focusing. Japanese Journal of Applied Physics, 2016, 55, 038001.	1.5	7
26	Crystalline property analysis of semipolar (20–21) GaN on (22–43) patterned sapphire substrate by Xâ€ray microdiffraction and transmission electron microscopy. Physica Status Solidi (B): Basic Research, 2015, 252, 1149-1154.	1.5	6
27	⁵⁷ Fe polarization-dependent synchrotron MössbauerÂspectroscopy using a diamond phaseÂplate and an iron borate nuclear BraggÂmonochromator. Journal of Synchrotron Radiation, 2015, 22, 427-435.	2.4	11
28	Controlling charge-density-wave states in nano-thick crystals of 1T-TaS2. Scientific Reports, 2014, 4, 7302.	3.3	126
29	Nanometer-Scale Characterization Technique for Si Nanoelectric Materials Using Synchrotron Radiation Microdiffraction. Key Engineering Materials, 2011, 470, 104-109.	0.4	6
30	High-Angular-Resolution Microbeam X-Ray Diffraction with CCD Detector. AIP Conference Proceedings, 2010, , .	0.4	25
31	Backscattering of α-Quartz (0 6 10) for 14.4 keV Mol^ssbauer Photons. AIP Conference Proceedings, 2007, ,	0.4	3
32	Stroboscopic topographies on iron borate crystal in 9.6 MHz rf magnetic field. Nuclear Instruments & Methods in Physics Research B, 2003, 199, 75-80.	1.4	4